Abstract

Quartz Glass Crucible For Producing Silicon Crystals And Process For Producing Quartz Glass Crucible

Quartz glass crucible for pulling a single crystal of silicon by the Czochralski method, having an inside on which is arranged an inner layer of quartz glass which forms a surface, wherein the inner layer is provided with a crystallization promoter which upon heating of the quartz glass crucible during use as intended in crystal pulling brings about a crystallization of quartz glass to form ß-cristobalite, characterized in that the concentration of synthetically obtained SiO_2 C at a distance d from the surface is greater than the concentration of synthetically obtained SiO_2 at a distance d2 from the surface, wherein d2 is greater than d.

Fig. 1